

TERMINAL ASSIGNMENT

CMOS Hex Voltage-Level Shifter for TTL-to-CMOS or CMOS-to-CMOS Operation

High-Voltage Types (20-Volt Rating)

Features:

- Independence of power-supply sequence considerations— V_{CC} can exceed V_{DD} ; input signals can exceed both V_{CC} and V_{DD}
- Up and down level-shifting capability
- Shiftable input threshold for either CMOS or TTL compatibility
- Standardized symmetrical output characteristics
- 100% tested for quiescent current @ 20 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5 V, 10 V, and 15 V parametric ratings
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

■ CD4504B hex voltage level-shifter consists of six circuits which shift input signals from the V_{CC} logic level to the V_{DD} logic level. To shift TTL signals to CMOS logic levels, the SELECT input is at the V_{CC} HIGH logic state. When the SELECT input is at a LOW logic state, each circuit translates signals from one CMOS level to another.

The CD4504B device is supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead plastic dual-in-line packages (E suffix), 16-lead dual-in-line surface-mount plastic packages (M suffix), and in chip form (H suffix).

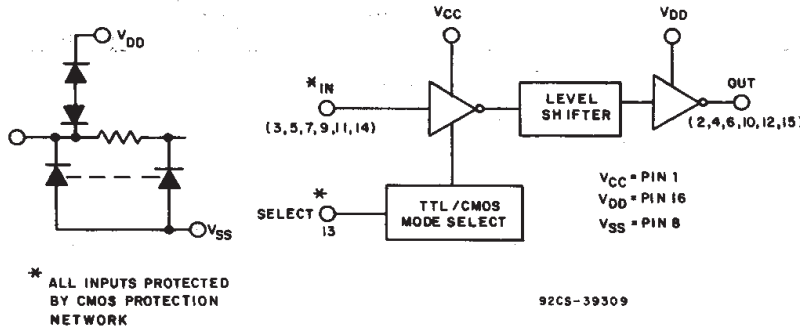


Fig. 1 - Functional diagram for CD4504B.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5V$

DC INPUT CURRENT, ANY ONE INPUT ± 10 mA

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500mW

For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$: Derate Linearly at 12mW/ $^\circ\text{C}$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR -

FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$

STORAGE TEMPERATURE RANGE (T_{stg}) -85°C to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10s max $+265^\circ\text{C}$

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4504B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS				LIMITS AT INDICATED TEMPERATURES (°C)							UNITS	
	V _O (V)	V _{IN} (V)	V _{CC} (V)	V _D (V)	-55	-40	+85	+125	+25				
									MIN	TYP	MAX		
Quiescent Device Current, I _{DD} Max and I _{CC} in CMOS-CMOS Mode	—	0,5	5	5	1	1	30	30	—	0.02	1	μA	
	—	0,10	5	10	2	2	60	60	—	0.02	2		
	—	0,15	5	15	4	4	120	120	—	0.02	4		
	—	0,20	5	20	20	20	600	600	—	0.04	20		
Quiescent Device Current, I _{CC} Max TTL-CMOS Mode	—	0,5	5	5	5	5	6	6	—	2.5	5	mA	
	—	0,10	5	10	5	5	6	6	—	2.5	5		
	—	0,15	5	15	5	5	6	6	—	2.5	5		
Output Low (Sink) Current, I _{OL} Min	0.4	0.5	—	5	0.64	0.61	0.42	0.36	0.51	1	—	mA	
	0.5	0,10	—	10	1.6	1.5	1.1	0.9	1.3	2.6	—		
	1.5	0,15	—	15	4.2	4	2.8	2.4	3.4	6.8	—		
Output High (Source) Current, I _{OH} Min	4.6	0,5	—	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA	
	2.5	0,5	—	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—		
	9.5	0,10	—	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—		
	13.5	0,15	—	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—		
Output Voltage: Low-Level, V _{OL} Max	—	0,5	—	5	0.05				—	0	0.05	V	
	—	0,10	—	10	0.05				—	0	0.05		
	—	0,15	—	15	0.05				—	0	0.05		
Output Voltage: High-Level, V _{OH} Min	—	0,5	—	5	4.95				4.95	5	—	V	
	—	0,10	—	10	9.95				9.95	10	—		
	—	0,15	—	15	14.95				14.95	15	—		
Input Low Voltage, V _{IL} Max Note 1	TTL-CMOS	1	—	5	10	0.8				—	—	0.8	V
	TTL-CMOS	1	—	5	15	0.8				—	—	0.8	
	CMOS-CMOS	1	—	5	10	1.5				—	—	1.5	
	CMOS-CMOS	1.5	—	5	15	1.5				—	—	1.5	
	CMOS-CMOS	1.5	—	10	15	3				—	—	3	
Input High Voltage, V _{IH} Min Note 1	TTL-CMOS	9	—	5	10	2				2	—	—	V
	TTL-CMOS	13.5	—	5	15	2				2	—	—	
	CMOS-CMOS	9	—	5	10	3.5				3.5	—	—	
	CMOS-CMOS	13.5	—	5	15	3.5				3.5	—	—	
	CMOS-CMOS	13.5	—	10	15	7				7	—	—	
Input Current, I _{IN} Max	—	0,18	—	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA	

Note 1: Applies to the 6 input signals. For mode control (P13), only the CMOS-CMOS ratings apply.

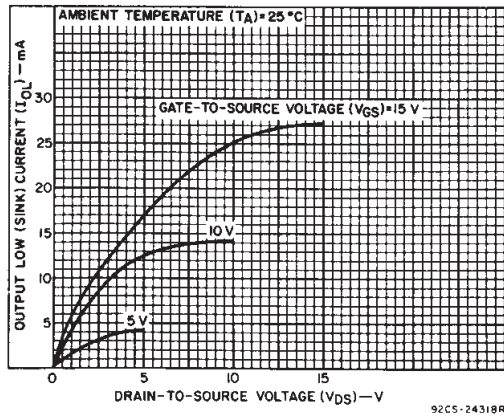


Fig. 2 - Typical output low (sink) current characteristics.

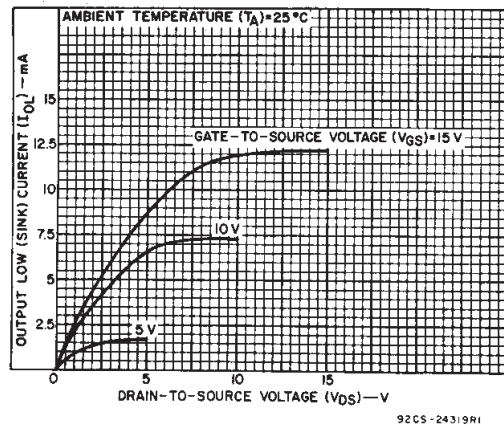
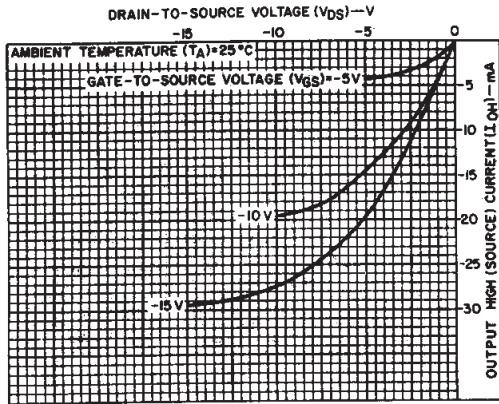


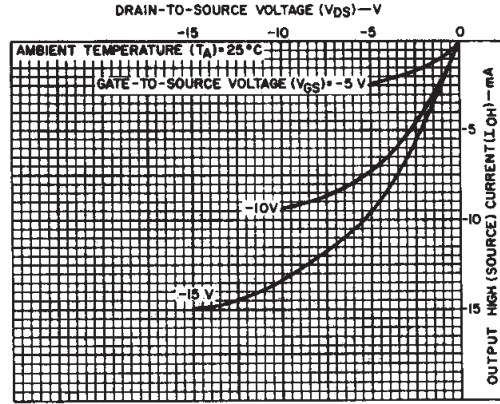
Fig. 3 - Minimum output low (sink) current characteristics.

CD4504B Types



92CS-24320R3

Fig. 4 - Typical output high (source) current characteristics.



92CS-24321R2

Fig. 5 - Minimum output high (source) current characteristics.

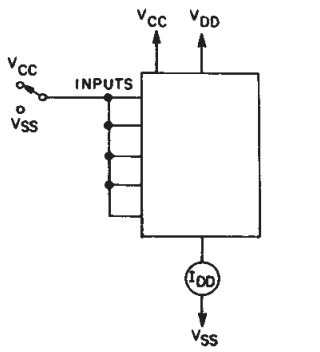
RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V _{DD} (V)	LIMITS		UNITS
		Min.	Max.	
Supply-Voltage Range (For T _A = Full Package-Temperature Range)	—	3	18	V

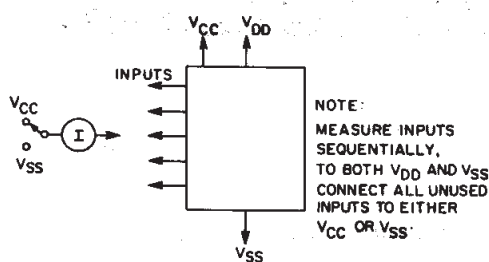
DYNAMIC ELECTRICAL CHARACTERISTICS, At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 Ω

CHARACTERISTIC	SHIFTING MODE	V _{CC} (V)	V _{DD} (V)	LIMITS		UNITS
				TYP.	MAX.	
Propagation Delay: High-to-Low, t _{PHL}	TTL to CMOS V _{DD} > V _{CC}	5	10	140	280	ns
	CMOS to CMOS V _{DD} > V _{CC}	5	10	120	240	
		5	15	120	240	
		10	15	70	140	
	CMOS to CMOS V _{CC} > V _{DD}	10	5	275	550	
		15	5	275	550	
		15	10	70	140	
Low-to-High, t _{PLH}	TTL to CMOS V _{DD} > V _{CC}	5	10	140	280	ns
	CMOS to CMOS V _{DD} > V _{CC}	5	10	120	240	
		5	15	120	240	
		10	15	70	140	
	CMOS to CMOS V _{CC} > V _{DD}	10	5	200	400	
		15	5	200	400	
		15	10	60	120	
Transition Time, t _{THL} , t _{TLH}	All Modes		5	100	200	ns
			10	50	100	
			15	40	80	
Input Capacitance, C _{IN}	Any Input			5	7.5	pF



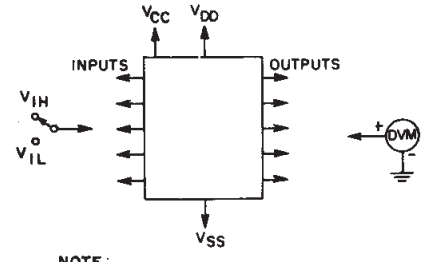
92CS-29452

Fig. 6 - Quiescent device current.



92CS-29454

Fig. 7 - Input current.



NOTE:
TEST ANY COMBINATION
OF INPUTS

92CS-29453

Fig. 8 - Input voltage.

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4504B Types

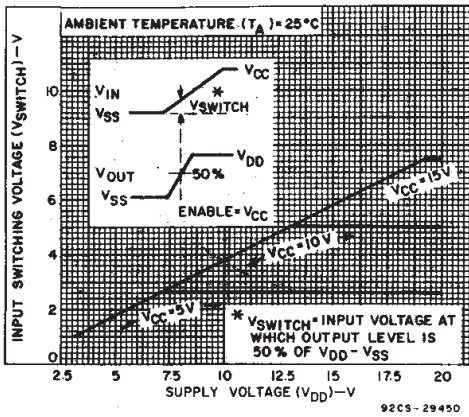


Fig. 9 - Typical input switching as a function of high-level supply voltage. (SELECT at V_{CC} -CMOS mode).

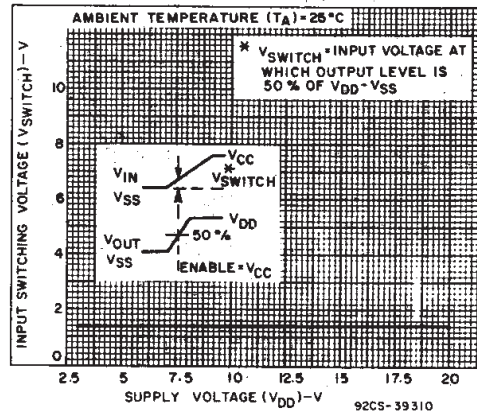


Fig. 10 - Typical input switching as a function of high-level supply voltage (SELECT at V_{SS} -TTL mode).

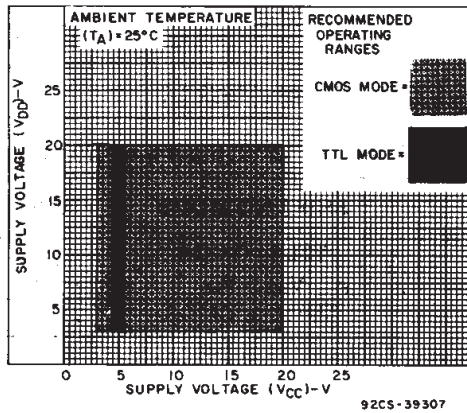
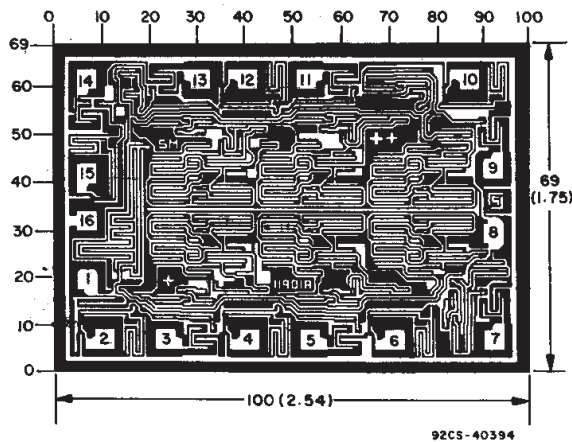


Fig. 11 - High-level supply voltage vs. low-level supply voltage.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and pad layout for CD4504BH.

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.